


# IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	Gregory G. Romas, Jr.	Docket No.:	TI-33156.1
Serial No	TBD	Art Unit:	2813
Filed:	Herewith	Examiner:	Schillinger, Laura
For:	Low Current Blow Trim Fuse	Confirm. No.:	TBD

## PRELIMINARY AMENDMENT

Mail Stop Patent Application  
Commissioner of Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

"EXPRESS MAIL" mailing label number EV 333320181  
US. I hereby certify that the Preliminary Amendment and the  
accompanying Application is being deposited with the United States  
Postal Service "Express Mail Post Office to Addressee" service under  
37 § CFR 1.10 on the above-mentioned date and is addressed to the  
Mail Stop Patent Application, Commissioner of Patents, P. O. Box  
1450, Alexandria, VA 22313-1450.

  
Allen B. Kroger

5/24/05  
DATE

Sir:

Before examination of the above-identified patent application, please make the following amendments:

### IN THE CLAIMS:

Please cancel Claims 1-7 and 10-15 and add new Claims 16-23 which are enclosed on separate pages herewith.

Respectfully submitted,



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**Claims:**

1-7 (cancelled)

8. (original) A method of forming a trim fuse comprising the steps of:

forming a stepped oxide region on a semiconductor substrate;

forming at least one thinned oxide region on said semiconductor substrate and proximal said stepped oxide region; and

depositing an electrically blowable fuse material on said stepped oxide region and said at least one thinned oxide region to form at least one transition region such that said fuse material changes in thickness as it transitions between said at least one thinned oxide region and said stepped oxide region.

9. (original) The method according to claim 8 wherein said step of depositing an electrically blowable fuse material on said stepped oxide region and said at least one thinned oxide region comprises forming said at least one transition region such that said fuse material reduces in thickness as it transitions from said at least one thinned oxide region to said stepped oxide region.

10-15 (canceled)

16. (new) The trim fuse according to Claim 8 wherein said fuse material comprises metal.

17. (new) The trim fuse according to Claim 9 wherein said fuse material comprises metal.

18. (new) The trim fuse according to Claim 16 wherein said metal comprises Al/Cu.
19. (new) The trim fuse according to Claim 17 wherein said metal comprises Al/Cu.
20. (new) The trim fuse according to Claim 8 wherein said fuse material comprises polycrystal silicon.
21. (new) The trim fuse according to Claim 9 wherein said fuse material comprises polycrystal silicon.
22. (new) The trim fuse according to Claim 8 wherein said semiconductor substrate comprises silicon.
23. (new) The trim fuse according to Claim 9 wherein said semiconductor substrate comprises silicon: